



HIGH SPEED, TRIPLE DIGITAL ISOLATORS

Check for Samples: ISO7230C, ISO7230M, ISO7231C, ISO7231M

FEATURES

- 25 and 150-Mbps Signaling Rate Options
 - Low Channel-to-Channel Output Skew;
 1 ns max
 - Low Pulse-Width Distortion (PWD);2 ns max
 - Low Jitter Content; 1 ns Typ at 150 Mbps
- Typical 25-Year Life at Rated Working Voltage (See Application Note SLLA197 and Figure 14)
- 4000-V_{peak} Isolation, 560-V_{peak} V_{IORM}
 - UL 1577, IEC 60747-5-2 (VDE 0884, Rev 2),
 IE 61010-1, IEC 60950-1 and CSA Approved
- 4 kV ESD Protection
- Operate With 3.3-V or 5-V Supplies

- High Electromagnetic Immunity (See Application Note SLLA181)
- –40°C to 125°C Operating Range

APPLICATIONS

- Industrial Fieldbus
- Computer Peripheral Interface
- Servo Control Interface
- Data Acquisition

DESCRIPTION

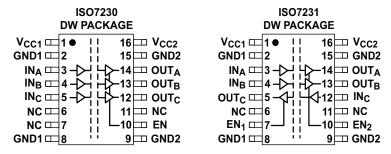
The ISO7230 and ISO7231 are triple-channel digital isolators each with multiple channel configurations and output enable functions. These devices have logic input and output buffers separated by Tl's silicon dioxide (SiO₂) isolation barrier. Used in conjunction with isolated power supplies, these devices block high voltage, isolate grounds, and prevent noise currents on a data bus or other circuits from entering the local ground and interfering with or damaging sensitive circuitry.

The ISO7230 triple-channel device has all three channels in the same direction while the ISO7231 has two channels in one direction and one channel in opposition. These devices have an active-high output enable that when driven to a low level, places the output in a high-impedance state.

The ISO7230C and ISO7231C have TTL input thresholds and a noise-filter at the input that prevents transient pulses of up to 2 ns in duration from being passed to the output of the device, while the ISO7230M and ISO7231M have CMOS $V_{CC}/2$ input thresholds and do not have the input noise-filter or the additional propagation delay.

In each device, a periodic update pulse is sent across the isolation barrier to ensure the proper dc level of the output. If this dc-refresh pulse is not received, the input is assumed to be unpowered or not being actively driven, and the failsafe circuit drives the output to a logic high state. (Contact TI for a logic low failsafe option).

These devices require two supply voltages of 3.3-V, 5-V, or any combination. All inputs are 5-V tolerant when supplied from a 3.3-V supply and all outputs are 4-mA CMOS. These devices are characterized for operation over the ambient temperature range of –40°C to 125°C.





Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.





This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

FUNCTION DIAGRAM

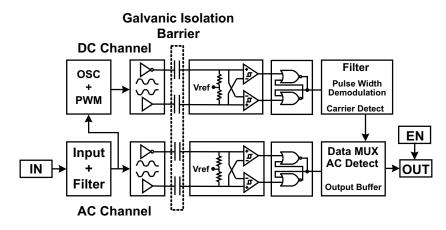


Table 1. Device Function Table ISO723x (1)

INPUT V _{CC}	OUTPUT V _{CC}	INPUT (IN)	OUTPUT ENABLE (EN)	OUTPUT (OUT)
		Н	H or Open	Н
PU	PU	L	H or Open	L
PU		X	Г	Z
		Open	H or Open	Н
PD	D PU X		H or Open	Н
PD	PU	X	L	Z

(1) PU = Powered Up; PD = Powered Down; X = Irrelevant; H = High Level; L = Low Level

AVAILABLE OPTIONS

PRODUCT	SIGNALING RATE	INPUT THRESHOLD	CHANNEL CONFIGURATION	MARKED AS	ORDERING NUMBER ⁽¹⁾			
ISO7230CDW	25 Mbps	~1.5 V (TTL)		ISO7230C	ISO7230CDW (rail)			
13072300000	25 Mibbs	(CMOS compatible)	3/0	13072300	ISO7230CDWR (reel)			
ISO7230MDW	150 Mbpo	\/aa/2 (CMOS)	3/0	ISO7230M	ISO7230MDW (rail)			
1507230101000	150 Mbps	Vcc/2 (CMOS)		1507230IVI	ISO7230MDWR (reel)			
ISO7231CDW	25 Mbno	~1.5 V (TTL)		ISO7231C	ISO7231CDW (rail)			
15072310000	25 Mbps	(CMOS compatible)	0/4	15072310	ISO7231CDWR (reel)			
ISO7231MDW	150 Mbps	Vee/2 (CMOC)	2/1	ISO7231M	ISO7231MDW (rail)			
1507231111011	150 Mbps	Vcc/2 (CMOS)		1507231W	ISO7231MDWR (reel)			

(1) For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI website at www.ti.com.



ABSOLUTE MAXIMUM RATINGS(1)

					VALUE	UNIT
V_{CC}	Supply voltag	je ⁽²⁾ , V _{CC1} , V _{CC2}			-0.5 to 6	V
V_{I}	Voltage at IN	, OUT, EN			-0.5 to 6	V
Io	Output current				±15	mA
		Human Body Model	JEDEC Standard 22, Test Method A114-C.01		±4	
ESD	Electrostatic discharge	Field-Induced-Charged Device Model	JEDEC Standard 22, Test Method C101	All pins	±1	kV
		Machine Model	ANSI/ESDS5.2-1996		±200	V
T_{J}	Maximum jun		170	°C		

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

			MIN	TYP	MAX	UNIT
V_{CC}	Supply voltage ⁽¹⁾ , V _{CC1} , V _{CC2}		3.15		5.5	V
I _{OH}	High-level output current				4	mA
I _{OL}	Low-level output current		-4			mA
	long to pulse width	ISO723xC	40			20
t _{ui}	Input pulse width	ISO723xM	6.67	5		ns
4 /4	Cionalia e vata	ISO723xC	0	30 ⁽²⁾	25	Maria
1/t _{ui}	Signaling rate	ISO723xM	0	200(2)	150	Mbps
V_{IH}	High-level input voltage (IN)	100702.44	0.7 V _{CC}		V _{CC}	V
V_{IL}	Low-level input voltage (IN)	- ISO723xM	0		0.3 V _{CC}	V
V_{IH}	High-level input voltage (IN) (EN on all devices)	100700.0	2		V _{CC}	
V_{IL}	Low-level input voltage (IN) (EN on all devices)	ISO723xC	0		0.8	V
T_J	Junction temperature				150	°C
Н	External magnetic field-strength immunity per IEC certification	C 61000-4-8 and IEC 61000-4-9			1000	A/m

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.

⁽²⁾ All voltage values are with respect to network ground terminal and are peak voltage values.

⁽²⁾ Typical sigalling rate under ideal conditions at 25°C.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V⁽¹⁾ OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT					,	
	10070000/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		1	3	Α
	ISO7230C/M	25 Mbps	EN ₂ at 3 V		7	9.5	mA
I _{CC1}	10070040/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		6.5	11	A
	ISO7231C/M	25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		11	17	mA
	ISO7230C/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		15	22	A
	1507230C/W	25 Mbps	EN ₂ at 3 V		17	24	mA
I _{CC2}	10070040/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no load,		13	20	A
	ISO7231C/M	25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		17.5	27	mA
ELECTR	RICAL CHARACTERISTI	cs		·			
I _{OFF}	Sleep mode output cu	rrent	EN at 0 V, Single channel		0		μA
V	Lligh lovel output volte		I _{OH} = -4 mA, See Figure 1	$V_{CC} - 0.8$ $V_{CC} - 0.1$			V
V_{OH}	High-level output volta	ige	I _{OH} = -20 μA, See Figure 1				V
V	Low-level output volta	20	I _{OL} = 4 mA, See Figure 1			0.4	V
V_{OL}	Low-level output voltage	ge	I _{OL} = 20 μA, See Figure 1			0.1	V
$V_{I(HYS)}$	Input voltage hysteres	is			150		mV
I _{IH}	High-level input currer	nt	IN from 0 \/ to \/			10	
I _{IL}	Low-level input current		IN from 0 V to V _{CC}	-10			μA
C _I	Input capacitance to g	round	IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		2		pF
CMTI	Common-mode transie	ent immunity	V _I = V _{CC} or 0 V, See Figure 4	25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 5-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay	ISO723xC	Soo Eiguro 1	18		42	ns
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	130723XC	See Figure 1			2.5	115
t _{PLH} , t _{PHL}	Propagation delay	ISO723xM		10		23	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	150723XIVI			1	2	ns
	Part-to-part skew (2)	ISO723xC				8	
t _{sk(pp)}	Part-to-part skew (-)	ISO723xM			0	3	ns
	Character shared system (3)	ISO723xC			0	2	
t _{sk(o)}	Channel-to-channel output skew (3)	ISO723xM			0	1	ns
t _r	Output signal rise time		See Figure 1		2		20
t _f	Output signal fall time		See Figure 1		2		ns
t _{PHZ}	Propagation delay, high-level-to-high-im	pedance output			15	20	
t _{PZH}	Propagation delay, high-impedance-to-h	igh-level output	Saa Firma O		15	20	
t _{PLZ}	Propagation delay, low-level-to-high-imp	edance output	See Figure 2		15	20	ns
t _{PZL}	Propagation delay, high-impedance-to-lo	ow-level output			15	20	
t _{fs}	Failsafe output delay time from input power loss		See Figure 3		12		μs
t _{jit(pp)}	Peak-to-peak eye-pattern jitter	ISO723xM	150 Mbps PRBS NRZ data input, Same polarity inputon all channels, See Figure 5		1		ns

⁽¹⁾ Also referred to as pulse skew.

⁽²⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V⁽¹⁾ OPERATION

	PARAMETE	R	TEST CONDITION	S	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT				•			
	ISO7230C/M	Quiescent	V V or OV All channels no la	$V_1 = V_{CC}$ or 0 V, All channels, no load, EN ₂ at 3 V		1	3	A
	1507230C/W	25 Mbps	V _I = V _{CC} or 0 V, All channels, no lo	au, ⊑N ₂ at 3 v		7	9.5	mA
I _{CC1}	ISO7231C/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no lo	ad, EN ₁ at 3 V,		6.5	11	mA
	1307231C/W	25 Mbps	EN ₂ at 3 V			11	17	ША
	ISO7230C/M	Quiescent	$V_I = V_{CC}$ or 0 V, All channels, no lo	and EN at 3 V		9	15	mA
	1307230C/W	25 Mbps	V _I = V _{CC} or 0 V, All charmers, no io	au, Liv ₂ at 3 v		10	17	ША
I _{CC2}	ISO7231C/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no lo	ad, EN ₁ at 3 V,		8	12	mA
	1307231C/W	25 Mbps	EN ₂ at 3 V			10.5	16	ША
ELECTR	ICAL CHARACTE	RISTICS						
I _{OFF}	Sleep mode outp	out current	EN at 0 V, Single channel		0		μΑ	
				ISO7230	$V_{CC} - 0.4$			
V_{OH}	High-level output	t voltage	I _{OH} = -4 mA, See Figure 1	ISO7231 (5-V side)	V _{CC} – 0.8			V
			$I_{OH} = -20 \mu A$, See Figure 1	I _{OH} = -20 μA, See Figure 1				
\/	Law laval autout	voltogo	I _{OL} = 4 mA, See Figure 1				0.4	V
V_{OL}	Low-level output	voltage	I _{OL} = 20 μA, See Figure 1				0.1	V
$V_{I(HYS)}$	Input voltage hys	steresis				150		mV
I _{IH}	High-level input	current	INI from O \/ to \/				10	
I _{IL}	Low-level input of	current	nt IN from 0 V to V _{CC}		-10			μΑ
C _I	Input capacitanc	e to ground	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$			2		pF
CMTI	Common-mode to immunity	transient	V _I = V _{CC} or 0 V, See Figure 4		25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} at 5-V, V_{CC2} at 3.3-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay, low-to-high-level output	100700	Con Figure 4	20		50	20
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO723xC	See Figure 1			3	ns
t _{PLH} , t _{PHL}	Propagation delay, low-to-high-level output	100700		12		29	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO723xM			1	2	ns
	Don't to a out allow (2)	ISO723xC				10	
t _{sk(pp)}	Part-to-part skew ⁽²⁾	ISO723xM			0	5	ns
	(3)	ISO723xC			0	2.5	
t _{sk(o)}	Channel-to-channel output skew (3)	ISO723xM			0	1	ns
t _r	Output signal rise time		0		2		
t _f	Output signal fall time		See Figure 1		2		ns
t _{PHZ}	Propagation delay, high-level-to-high-impeda	nce output			15	20	
t _{PZH}	Propagation delay, high-impedance-to-high-le	evel output	0		15	20	
t _{PLZ}	Propagation delay, low-level-to-high-impedar	ice output	See Figure 2		15	20	ns
t _{PZL}	Propagation delay, high-impedance-to-low-level output				15	20	
t _{fS}	Failsafe output delay time from input power loss		See Figure 3		18		μs
t _{jit(pp)}	Peak-to-peak eye-pattern jitter ISO723xM		150 Mbps PRBS NRZ data input, Same polarity input on all channels, See Figure 5		1		ns

⁽¹⁾ Also known as pulse skew

t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} at 3.3-V, V_{CC2} at 5-V⁽¹⁾ OPERATION

	PARAMETE	R	TEST CONDITIONS		MIN	TYP	MAX	UNIT
SUPPLY	CURRENT							
	ISO7230C/M	Quiescent	// // or 0 // All channels no lea	d FN at 2.1/		0.5	1	A
	1507230C/W	25 Mbps	$V_I = V_{CC}$ or 0 V, All channels, no loa	u, EIN ₂ at 3 V		3	5	mA
I _{CC1}	ISO7231C/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no loa	d, EN ₁ at 3 V,		4.5	7	mA
	1307231C/W	25 Mbps	EN ₂ at 3 V			6.5	11	ША
	ISO7230C/M	Quiescent	$V_I = V_{CC}$ or 0 V, All channels, no loa	d EN at 2 V		15	22	mA
	1307230C/W	25 Mbps	V ₁ = V _{CC} or 0 V, All charmers, no loa	u, Liv ₂ at 3 v		17	24	ША
I _{CC2}	ISO7231C/M	Quiescent	V _I = V _{CC} or 0 V, All channels, no loa	d, EN ₁ at 3 V,		13	20	mA
	1307231C/W	25 Mbps	EN ₂ at 3 V			17.5	27	ША
ELECTR	ICAL CHARACTE	RISTICS						
I _{OFF}	Sleep mode outp	out current	EN at 0 V, Single channel			0		μΑ
			I _{OH} = -4 mA, See Figure 1	ISO7230	V _{CC} - 0.4			
V_{OH}	High-level output	: VOITAGE		ISO7231 (5-V side)	V _{CC} - 0.8			V
			$I_{OH} = -20 \mu A$, See Figure 1		V _{CC} - 0.1			
1/	Law laval autout	voltogo	I _{OL} = 4 mA, See Figure 1				0.4	V
V_{OL}	Low-level output	voltage	I _{OL} = 20 μA, See Figure 1	I _{OL} = 20 μA, See Figure 1			0.1	V
V _{I(HYS)}	Input voltage hys	steresis				150		mV
I _{IH}	High-level input	current	INI france O V/ to V/				10	
I _{IL}	Low-level input of	w-level input current IN from 0 V to V _{CC}		-10			μΑ	
C _I	Input capacitanc	e to ground	IN at V_{CC} , $V_{I} = 0.4 \sin (4E6\pi t)$			2		pF
CMTI	Common-mode to immunity	transient	V _I = V _{CC} or 0 V, See Figure 4		25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} at 3.3-V and V_{CC2} at 5-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay	1007000		22		51	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO723xC				3	
t _{PLH} , t _{PHL}	Propagation delay	100700 14	See Figure 1	12		30	ns
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO723xM			1	2	
	Part-to-part skew (2)					10	
t _{sk(pp)}	Part-to-part skew (=/	ISO723xM			0	5	ns
	Ob (3)	ISO723xC			0	2.5	
t _{sk(o)}	Channel-to-channel output skew (3)	ISO723xM			0	1	ns
t _r	Output signal rise time		Con Figure 4		2		
t _f	Output signal fall time		See Figure 1		2		ns
t _{PHZ}	Propagation delay, high-level-to-high-impedar	ice output			15	20	
t _{PZH}	Propagation delay, high-impedance-to-high-le	vel output	See Figure 2		15	20	no
t _{PLZ}	Propagation delay, low-level-to-high-impedance	ce output	See Figure 2		15	20	ns
t _{PZL}	Propagation delay, high-impedance-to-low-lev	el output			15	20	
t _{fs}	Failsafe output delay time from input power loss		See Figure 3		12		μs
t _{jit(pp)}	Peak-to-peak eye-pattern jitter	ISO723xM	150 Mbps PRBS NRZ data input, Same polarity input on all channels, See Figure 5		1		ns

⁽¹⁾ Also known as pulse skew

⁽²⁾ $t_{sk(pp)}$ is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices operate with the same supply voltages, at the same temperature, and have identical packages and test circuits.

⁽³⁾ t_{sk(o)} is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the same direction while driving identical specified loads.



ELECTRICAL CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3 $V^{(1)}$ OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
SUPPLY	CURRENT			<u>.</u>			
	ISO7230C/M	Quiescent	V _I = V _{CC} or 0 V, all channels, no load,		0.5	1	mA
	1507230C/W	25 Mbps	EN ₂ at 3 V		3	5	MA
I _{CC1}	ISO7231C/M	Quiescent	V _I = V _{CC} or 0 V, all channels, no load,		4.5	7	mA
	1507231C/W	25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		6.5	11	MA
	ISO7230C/M	Quiescent	V _I = V _{CC} or 0 V, all channels, no load,		9	15	mA
	1507230C/W	25 Mbps	EN ₂ at 3 V		10	17	MA
I _{CC2}	10070040/M	Quiescent	V _I = V _{CC} or 0 V, all channels, no load,		8	12	A
	ISO7231C/M	25 Mbps	EN ₁ at 3 V, EN ₂ at 3 V		10.5	16	mA
ELECTR	ICAL CHARACTERISTICS	·					
I _{OFF}	Sleep mode output current		EN at 0 V, single channel		0		μA
\/	High lovel output voltage		I _{OH} = -4 mA, See Figure 1	V _{CC} - 0.4			V
V _{OH}	nigri-level output voltage		$I_{OH} = -20 \mu A$, See Figure 1	V _{CC} - 0.1			V
\/	Low level output voltage		I _{OL} = 4 mA, See Figure 1			0.4	V
V_{OL}	Low-level output voltage		I _{OL} = 20 μA, See Figure 1			0.1	V
$V_{I(HYS)}$	Input voltage hysteresis				150		mV
I _{IH}	High-level input current		IN from 0 V or V _{CC}			10	
I _{IL}	Low-level input current	rel output voltage el output voltage ltage hysteresis rel input current el input current	IN HOLL O A OL ACC	-10	-10		μA
Cı	Input capacitance to ground		IN at V_{CC} , $V_I = 0.4 \sin (4E6\pi t)$		2		pF
CMTI	Common-mode transient imn	nunity	V _I = V _{CC} or 0 V, See Figure 4	25	50		kV/μs

⁽¹⁾ For the 5-V operation, V_{CC1} or V_{CC2} is specified from 4.5 V to 5.5 V. For the 3-V operation, V_{CC1} or V_{CC2} is specified from 3.15 V to 3.6 V.



SWITCHING CHARACTERISTICS: V_{CC1} and V_{CC2} at 3.3-V OPERATION

	PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{PLH} , t _{PHL}	Propagation delay	10072240	See Figure 4	25		56	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	ISO723xC	See Figure 1			4	ns
t _{pLH} , t _{pHL}	Propagation delay	ISO723xM		12		34	
PWD	Pulse-width distortion ⁽¹⁾ t _{PHL} - t _{PLH}	150723XIVI			1	2	ns
	Part-to-part skew (2)	ISO723xC				10	
t _{sk(pp)}	Part-to-part skew V	ISO723xM			0	5	ns
	Channel-to-channel output skew (3)	ISO723xC			0	3	
t _{sk(o)}	Channel-to-channel output skew (5)	ISO723xM			0	1	ns
t _r	Output signal rise time		See Figure 1		2		
t _f	Output signal fall time				2		ns
t _{PHZ}	Propagation delay, high-level-to-high-impe	dance output			15	20	
t _{PZH}	Propagation delay, high-impedance-to-high	n-level output	Con Firm 0		15	20	
t _{PLZ}	Propagation delay, low-level-to-high-imped	lance output	See Figure 2		15	20	ns
t _{PZL}	Propagation delay, high-impedance-to-low-level output				15	20	
t _{fs}	Failsafe output delay time from input power loss		See Figure 3		18		μs
t _{jit(pp)}	Peak-to-peak eye-pattern jitter	ISO723xM	150 Mbps PRBS NRZ data input, same polarity input on all channels, See Figure 5		1		ns

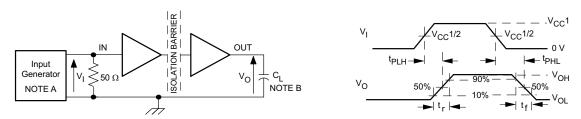
Also referred to as pulse skew.

t_{sk(pp)} is the magnitude of the difference in propagation delay times between any specified terminals of two devices when both devices (2)operate with the same supply voltages, at the same temperature, and have identical packages and test circuits. $t_{sk(0)}$ is the skew between specified outputs of a single device with all driving inputs connected together and the outputs switching in the

same direction while driving identical specified loads.

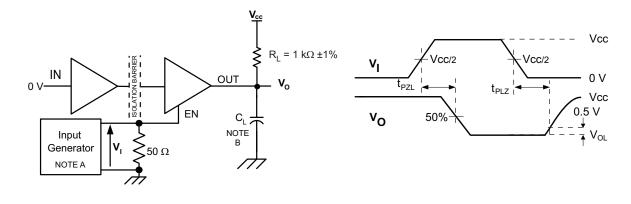


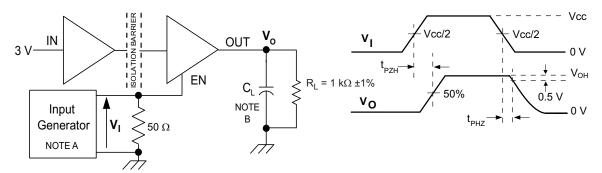
PARAMETER MEASUREMENT INFORMATION



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 1. Switching Characteristic Test Circuit and Voltage Waveforms



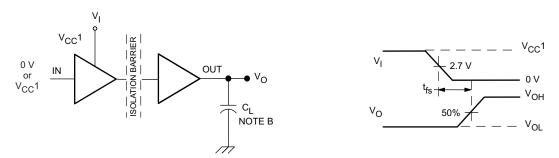


- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 2. Enable/Disable Propagation Delay Time Test Circuit and Waveform

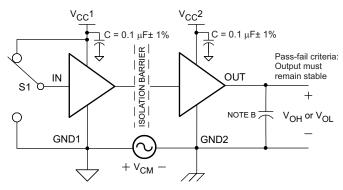


PARAMETER MEASUREMENT INFORMATION (continued)



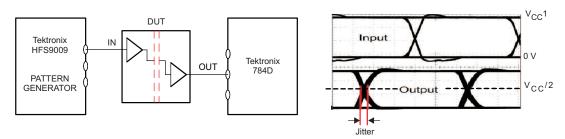
- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15$ pF and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 3. Failsafe Delay Time Test Circuit and Voltage Waveforms



- A. The input pulse is supplied by a generator having the following characteristics: PRR \leq 50 kHz, 50% duty cycle, $t_r \leq$ 3 ns, $t_f \leq$ 3 ns, $Z_O = 50\Omega$.
- B. $C_L = 15 \text{ pF}$ and includes instrumentation and fixture capacitance within $\pm 20\%$.

Figure 4. Common-Mode Transient Immunity Test Circuit and Voltage Waveform



NOTE: PRBS bit pattern run length is $2^{16} - 1$. Transition time is 800 ps. NRZ data input has no more than five consecutive 1s or 0s.

Figure 5. Peak-to-Peak Eye-Pattern Jitter Test Circuit and Voltage Waveform



DEVICE INFORMATION

PACKAGE CHARACTERISTICS

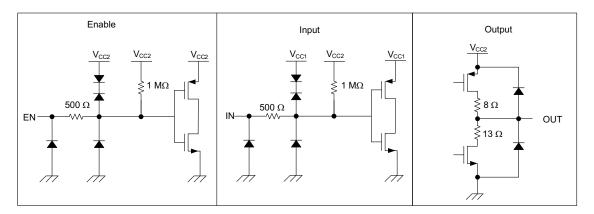
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
L(I01)	Minimum air gap (Clearance)	Shortest terminal-to-terminal distance through air	8.34			mm
L(I02)	Minimum external tracking (Creepage)	Shortest terminal-to-terminal distance across the package surface	8.1			mm
	Minimum Internal Gap (Internal Clearance)	Distance through the insulation	0.008			mm
R _{IO}	Isolation resistance	Input to output, V_{IO} = 500 V, all pins on each side of the barrier tied together creating a two-terminal device, T_A < 100°C		>10 ¹²		Ω
		Input to output, $V_{IO} = 500 \text{ V}$, $100^{\circ}\text{C} \le T_{A} \le T_{A} \text{ max}$		>10 ¹¹		Ω
C _{IO}	Barrier capacitance Input to output	$V_1 = 0.4 \sin (4E6\pi t)$		2		pF
CI	Input capacitance to ground	$V_1 = 0.4 \sin (4E6\pi t)$		2		рF

REGULATORY INFORMATION

VDE	CSA	UL
Certified according to IEC 60747-5-2	Approved under CSA Component Acceptance Notice	Recognized under 1577 Component Recognition Program ⁽¹⁾
File Number: 40016131	File Number: 1698195	File Number: E181974

⁽¹⁾ Production tested ≥ 3000 VRMS for 1 second in accordance with UL 1577.

DEVICE I/O SCHEMATICS



THERMAL CHARACTERISTICS

over recommended operating conditions (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
0	lunction to air	Low-K Thermal Resistance ⁽¹⁾	168			°C/W
θ _{JA} Junction-to-air		High-K Thermal Resistance		96.1		C/VV
θ_{JB}	Junction-to-Board Thermal Resistance			61		°C/W
θ_{JC}	Junction-to-Case Thermal Resistance			48		°C/W
P_D	Device Power Dissipation	$V_{CC1} = V_{CC2} = 5.5 \text{ V}, T_J = 150^{\circ}\text{C}, C_L = 15 \text{ pF},$ Input a 50% duty cycle square wave			220	mW

(1) Tested in accordance with the Low-K or High-K thermal metric definitions of EIA/JESD51-3 for leaded surface mount packages.



TYPICAL CHARACTERISTIC CURVES

ISO7230 C/M RMS SUPPLY CURRENT

Figure 6.

Signaling Rate - Mbps

ISO7231 C/M RMS SUPPLY CURRENT

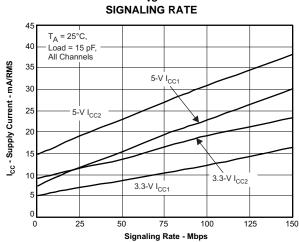


Figure 7.

PROPAGATION DELAY vs FREE-AIR TEMPERATURE

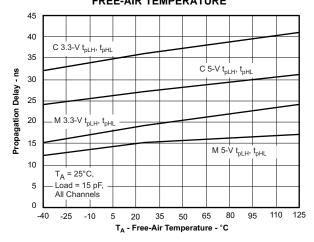


Figure 8.

INPUT THRESHOLD VOLTAGE vs FREE-AIR TEMPERATURE

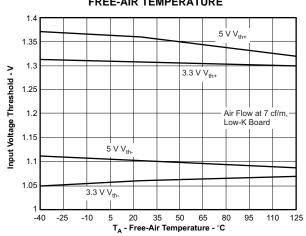
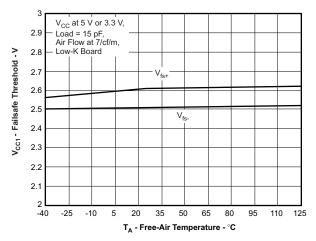


Figure 9.



TYPICAL CHARACTERISTIC CURVES (continued)

V_{CC1} FAILSAFE THRESHOLD vs FREE-AIR TEMPERATURE



HIGH-LEVEL OUTPUT CURRENT
vs
HIGH-LEVEL OUTPUT VOLTAGE

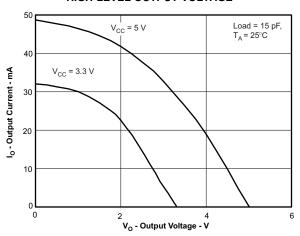
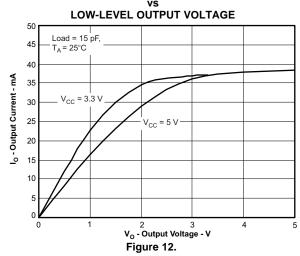


Figure 10. Figure 11.

LOW-LEVEL OUTPUT CURRENT





APPLICATION INFORMATION

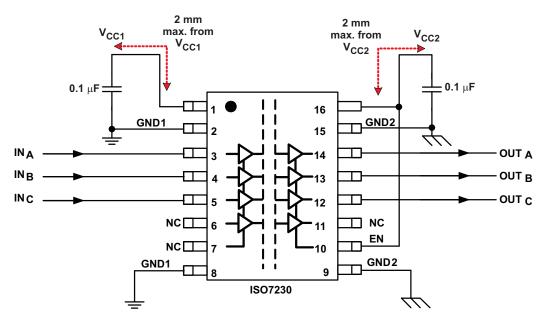


Figure 13. Typical ISO7230 Application Circuit

LIFE EXPECTANCY vs WORKING VOLTAGE

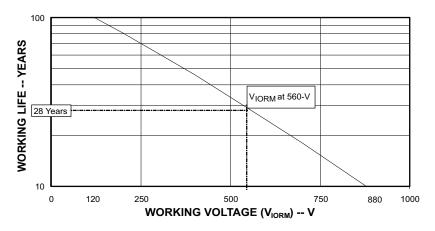


Figure 14. Time Dependant Dielectric Breakdown Testing Results



REVISION HISTORY

Changes from	om Original (September 2007) to Revision A	Page
• Deleted	Product Preview note	2
 Changed 	d V _{CC} Supply Voltage of the ROC Table From: 3 To: 3.15	3
 Changed 	d From: 3.6 To: 3.45	3
 Changed 	d TBD to actual values	4
 Changed 	d V _{CC} – 0.4 To: V _{CC} – 0.8	4
 Changed 	d C _I - Typical value from 1 To: 2	4
 Changed 	d Propagation delay max From: 22 To: 23	5
 Changed 	d C _I - Typical value from 1 To: 2	6
 Changed 	d Propagation delay max From: 46 To: 50	7
 Changed 	d Propagation delay max From: 28 To: 29	7
 Changed 	d C _I - Typical value from 1 To: 2	8
 Changed 	d Propagation delay max From: 26 To: 30	9
 Changed 	d C _I - Typical value from 1 To: 2	10
 Changed 	d Propagation delay max From: 32 To: 34	11
 Changed 	d C _{IO} - Typical value from 1 To: 2	14
 Changed 	d C _I - Typical value from 1 To: 2	14
 Changed 	d the REGULATORY INFORMATION Table	14
 Changed 	d Figure 6, Figure 7, and Figure 8	15
Changes from	om Revision A (December 2007) to Revision B	Page
• Changed	d Supply Voltage of the ROC Table From: 3.45 To: 3.6	3
Changes fro	om Revision B (April 2008) to Revision C	Page
	Min = 4.5 V and max = 5.5 V for Supply Voltage of the ROC Table	
	d Supply Voltage of the ROC Table From: 3.6 To: 5.5	
Change	3 Supply Voltage of the ROC Table From: 3.6 To: 5.5	
Changes fro	om Revision C (April 2008) to Revision D	Page
Changed	d Features bullet 4000-V _{peak} Isolation to the Features list	1
 Added t_s 	_{k(pp)} Part-to-part skew	5
	_{kk(pp)} Part-to-part skew	
	_{kk(pp)} Part-to-part skew	
	_{kk(pp)} Part-to-part skew	
 Changed 	Typical ISO723x Application Circuit Figure 13	17



Ci	langes from Revision D (May 2006) to Revision E	Page
•	Added Note: For the 5-V operation, VCC1 or VCC2 is specified from 4.5 V to 5.5 V. For the 3-V operation, VCC1 or VCC2 is specified from 3.15 V to 3.6 V.	
•	Added Note: For the 5-V operation, VCC1 or VCC2 is specified from 4.5 V to 5.5 V. For the 3-V operation, VCC1 or VCC2 is specified from 3.15 V to 3.6 V.	
•	Added Note: For the 5-V operation, VCC1 or VCC2 is specified from 4.5 V to 5.5 V. For the 3-V operation, VCC1 or VCC2 is specified from 3.15 V to 3.6 V.	
•	Added Note: For the 5-V operation, VCC1 or VCC2 is specified from 4.5 V to 5.5 V. For the 3-V operation, VCC1 or VCC2 is specified from 3.15 V to 3.6 V.	
•	Added Note: For the 5-V operation, VCC1 or VCC2 is specified from 4.5 V to 5.5 V. For the 3-V operation, VCC1 or VCC2 is specified from 3.15 V to 3.6 V.	
Cł	nanges from Revision E (June 2008) to Revision F	Page
•	Deleted device numbers ISO7230A and ISO7231A from the data sheet.	1
•	Deleted text from the Description "and turns off internal bias circuitry to conserve power"	1
•	Added t _{sk(pp)} footnote.	5
•	Added t _{sk(o)} footnote.	
•	Added t _{sk(pp)} footnote.	11
•	Added t _{sk(o)} footnote.	
•	Changed the PACKAGE CHARACTERISTICS table, line 1, L _(IO1) MIN from 7.7 to 8.34	14
Cł	nanges from Revision F (December 2008) to Revision G	Page
•	Added IEC 60950-1 and CSA Approved to the Features list	1
Cł	nanges from Revision G (September 2009) to Revision H	Page
•	Changed The Input circuit in the DEVICE I/O SCHEMATICS illustration	14

PACKAGE OPTION ADDENDUM

www.ti.com 3-Sep-2009

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
ISO7230CDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230CDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230CDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230CDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230MDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230MDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230MDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7230MDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231CDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231CDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231CDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231CDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231MDW	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231MDWG4	ACTIVE	SOIC	DW	16	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231MDWR	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
ISO7231MDWRG4	ACTIVE	SOIC	DW	16	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.



PACKAGE OPTION ADDENDUM

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(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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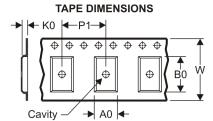
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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

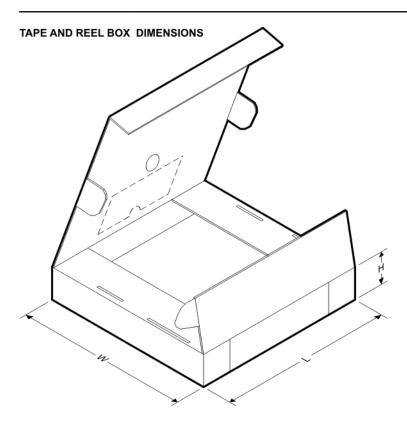
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All differsions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
ISO7230CDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7230MDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7231CDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1
ISO7231MDWR	SOIC	DW	16	2000	330.0	16.4	10.75	10.7	2.7	12.0	16.0	Q1

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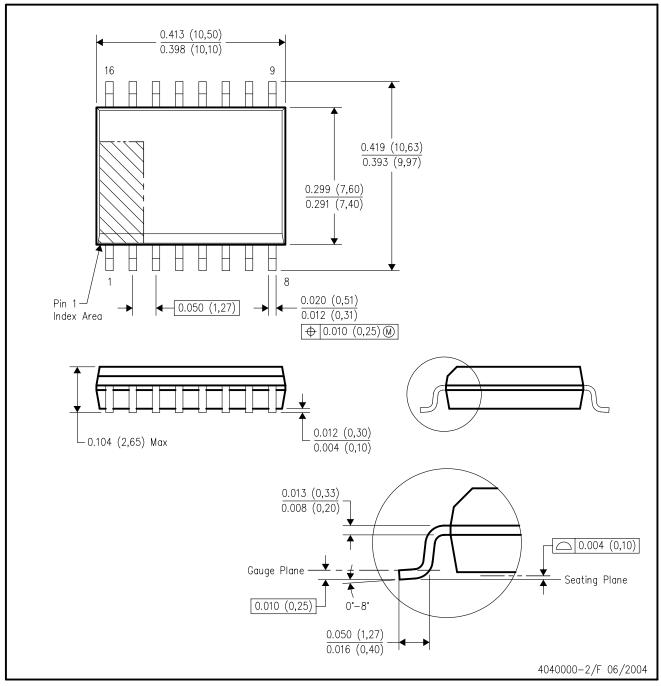


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
ISO7230CDWR	SOIC	DW	16	2000	358.0	335.0	35.0
ISO7230MDWR	SOIC	DW	16	2000	358.0	335.0	35.0
ISO7231CDWR	SOIC	DW	16	2000	358.0	335.0	35.0
ISO7231MDWR	SOIC	DW	16	2000	358.0	335.0	35.0

DW (R-PDSO-G16)

PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AA.



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RFID	www.ti-rfid.com	Space, Avionics & Defense	www.ti.com/space-avionics-defense
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